



AMERICAN
MICROSEMICONDUCTOR

BAV33 Diodes

General Purpose UHF/MW Mixer Diode

Military/High-Rel N

V(RRM)(V) Rep.Pk.Rev. Voltage

BandS

Test Freq 3.1G

Frequency Min. (Hz)

Frequency Max. (Hz)

V(FM) Max.(V) Forward Voltage

Ct{Cj} Nom. (F) Junction Cap.

NR Max.

Noise Figure Max. (dB) 6.5

Maximum Conversion Loss (dB)

I(RM) Max.(A) Reverse Current

Inp VSWR Max. 1.8

If Imped. Min 100

If Imped. Max. 200

Power In (test) 2.0m

R(load) (Ohms)

Zm (test)

Burnout Abs Max.

Semiconductor Material Silicon

Maximum Operating Temp (øC) 150b